

# SSDM 2003 Condensed Program

Tuesday, September 16							
EMINENCE HALL							
9:30 - 12:30 PL: Opening Session							
Room A	Room B	Room C	Room D	Room E	Room F	Room G	
14:00-15:50 A-1: Advanced Silicon Devices and Device Physics -Gate Stack Technologies- (5 papers)	14:00-16:00 B-1: Non-Volatile Memory Technologies -Non-Volatile Memory I- (5 papers)	14:00-15:50 C-1: Silicon Process / Materials Technologies -High-k Gate Dielectric I- (5 papers)	14:00-16:00 D-1: New Characterization -Oxide Reliability Characterization- (6 papers)	Materials and Surface	14:00-16:00 E-1: Quantum Nanostructure Devices and Physics -Fabrication and Micromechanics- (7 papers)	14:00-16:00 F-1: Compound Semiconductor Materials and Devices -III-V and Nitride Electron Devices- (7 papers)	14:00-15:50 G-1: Advanced Silicon Circuits and Systems -Advanced CMOS Circuits and Systems- (5 papers)
16:15-18:15 A-2: Advanced Silicon Devices and Device Physics -Advanced CMOS Technology I- (6 papers)	16:15-17:35 B-2: Non-Volatile Memory Technologies -Non-Volatile Memory II- (4 papers)	16:15-17:55 C-2: Silicon Process / Materials Technologies -High-k Gate Dielectric II- (5 papers)	16:15-18:15 D-2: New Characterization -Low k and Characterization- (6 papers)	Materials and Silicide	16:15-18:00 E-2: Quantum Nanostructure Devices and Physics -Nanostructured Optical Devices- (6 papers)	16:15-18:00 F-2: Compound Semiconductor Materials and Devices -Nitride Electron Devices- (6 papers)	16:15-17:45 G-2: Advanced Silicon Circuits and Systems -Collaboration of Circuits and Devices- (4 papers)
18:30-20:30 Banquet, Eminence Hall							
Wednesday, September 17							
Room A	Room B	Room C	Room D	Room E	Room F	Room G	
9:00-10:30 A-3: Advanced Silicon Devices and Device Physics -High-k Technology I- (4 papers)	9:00-10:20 B-3: Non-Volatile Memory Technologies -Non-Volatile Memory III- (3 papers)	9:00-10:30 C-3: Silicon Process / Materials Technologies -Memory Technology- (4 papers)	9:00-10:30 D-3: Silicon-Technologies -SOI Novel (4 papers)	on-Insulator Devices-	9:00-10:15 E-3: Quantum Nanostructure Devices and Physics -Characterization and Nanoprobing- (5 papers)	9:00-10:15 F-3: Compound Semiconductor Materials and Devices -Novel Compound Semiconductors Devices- (3 papers)	9:00-10:30 G-3: Advanced Silicon Circuits and Systems -Circuit Technologies for Emerging Technologies- (4 papers)
10:45-12:00 A-4: Optoelectronic Devices and Photonic Crystal Devices -VCSELs and Visible Lasers- (4 papers)	10:45-12:05 B-4: Non-Volatile Memory Technologies -Non-Volatile Memory IV- (4 papers)	10:45-12:05 C-4: Silicon Process / Materials Technologies -DRAM- (4 papers)	10:45-12:05 D-4: Silicon-Technologies -SOI Device (4 papers)	on-Insulator Physics-	10:45-12:15 E-4: Quantum Nanostructure Devices and Physics -Spin-related Phenomena- (5 papers)	10:45-12:15 F-4: Compound Semiconductor Materials and Devices -Optical Devices- (5 papers)	10:45-11:45 G-4: System-Level Integration and Packaging Technologies -System-Level Integration and Packaging Technologies I- (3 papers)
13:00-15:00 Poster Session (OHGI)							
15:15-16:45 A-5: Optoelectronic Devices and Photonic Crystal Devices -Optoelectronic Integrated Devices- (5 papers)	15:15-16:30 B-5: Organic Semiconductor Devices and Materials -Preparation and Characterization- (5 papers)	15:15-16:45 C-5: Silicon Process / Materials Technologies -Interconnect- (4 papers)	15:15-16:45 D-5: Silicon-Technologies -Fin FET (4 papers)	on-Insulator Technologies-	15:15-16:30 E-5: Quantum Nanostructure Devices and Physics -Single Electron Transport- (4 papers)	15:15-16:45 F-5: Micro-Nano Electromechanical Devices for Bio- and Chemical Applications -Micro-Nano Electro Mechanical Devices for Bio-and Chemical Applications I- (5 papers)	15:15-16:45 G-5: System-Level Integration and Packaging Technologies -System-Level Integration and Packaging Technologies II- (4 papers)
17:00-18:15 A-6: Optoelectronic Devices and Photonic Crystal Devices -Lasers for Optical Communication- (4 papers)	17:00-17:40 B-6: Non-Volatile Memory Technologies -Non-Volatile Memory V- (2 papers)	17:00-18:20 C-6: Silicon Process / Materials Technologies -Interconnect- (4 papers)	17:00-18:30 D-6: New Characterization -Si/SiGe Materials- (4 papers)	Materials and Devices and	17:00-18:30 E-6: Novel Devices, Physics, and Fabrication -Nanoprocess and Nanodevices- (5 papers)	17:00-18:00 F-6: Micro-Nano Electromechanical Devices for Bio- and Chemical Applications -Micro-Nano Electro Mechanical Devices for Bio-and Chemical Applications II- (3 papers)	17:00-18:15 G-6: System-Level Integration and Packaging Technologies -System-Level Integration and Packaging Technologies III- (4 papers)
18:45-20:45 Rump Session Room A “Can channel material/structure engineering become a guiding principle for future CMOS device technology?” Room B “What paradigm can nanoelectronic devices bring about?”							
Thursday, September 18							
Room A	Room B	Room C	Room D	Room E	Room F	Room G	
9:00-10:30 A-7: Advanced Silicon Devices and Device Physics -High-k Technology II- (4 papers)	9:00-10:20 B-7: Silicon Process / Materials Technologies -Metal Gate, Gate Oxide- (4 papers)	9:15-10:30 C-7: Organic Semiconductor Devices and Materials -Organic Thin Film Transistor- (4 papers)	9:20-10:30 D-7: New Characterization -Carbon Devices and (3 papers)	Materials and Nanotube Materials-	9:30-10:30 E-7: Novel Devices, Physics, and Fabrication -Novel Materials and Devices- (4 papers)	9:00-10:30 F-7: Optoelectronic Devices and Photonic Crystal Devices -Photonic Crystal Devices I- (5 papers)	9:00-10:30 G-7: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications -III-V Devices & Circuits- (5 papers)
10:45-12:05 A-8: Advanced Silicon Devices and Device Physics -Advanced CMOS Technology II- (4 papers)	10:45-12:05 B-8: Silicon Process / Materials Technologies -Si Process- (4 papers)	10:45-12:00 C-8: Organic Semiconductor Devices and Materials -Organic Optics- (5 papers)	10:45-11:25 D-8: New Characterization -High-k (2 papers)	Materials and Dielectrics I-	10:45-12:00 E-8: Novel Devices, Physics, and Fabrication -Carbon Nanotubess- (4 papers)	10:45-11:45 F-8: Optoelectronic Devices and Photonic Crystal Devices -Photonic Crystal Devices II- (3 papers)	10:45-11:45 G-8: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications -SiGe Technologies- (3 papers)
13:30-14:50 A-9: Advanced Silicon Devices and Device Physics -Electron Mobility Characteristics- (4 papers)	13:30-14:40 B-9: Silicon-on-Insulator Technologies -SOI Low Power Applications- (3 papers)	13:30-14:45 C-9: Organic Semiconductor Devices and Materials -Molecular Devices and Materials- (4 papers)	13:30-14:30 D-9: New Characterization -High-k (3 papers)	Materials and Dielectrics II-	13:30-14:30 E-9: Novel Devices, Physics, and Fabrication -Si Nanowire and Dots- (4 papers)	13:30-14:45 F-9: Optoelectronic Devices and Photonic Crystal Devices -Ultrafast Photonic Devices- (4 papers)	13:30-14:45 G-9: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications -GaN Devices- (4 papers)
15:00-16:00 A-10: Advanced Silicon Devices and Device Physics -Poly-Si Device and Sensor- (3 papers)	15:00-16:30 B-10: Silicon-on-Insulator Technologies -SOI CMOS Technologies- (4 papers)	15:00-16:00 C-10: Organic Semiconductor Devices and Materials -Electroluminescent Devices and Materials- (4 papers)	15:00-16:20 D-10: New Characterization -High-k (4 papers)	Materials and DielectricsIII-	15:00-16:15 E-10: Novel Devices, Physics, and Fabrication -Quantum Computing Devices- (4 papers)	15:00-16:00 F-10: Optoelectronic Devices and Photonic Crystal Devices -New Photonic Materials- (4 papers)	15:00-16:00 G-10: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications -High Voltage Devices- (3 papers)